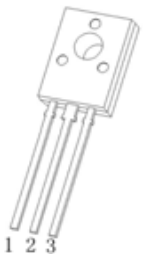
JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

TO-126C Plastic-Encapsulate Transistors

2SA1357 TRANSISTOR (PNP)

TO – 126C

1. EMITTER
2. COLLECTOR
3. BASE



FEATURES

- High Collector Current
- Strobe Flash Applications
- Audio Power Amplifier Applications

MAXIMUM RATINGS (T_a=25℃ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	-35	V
V_{CEO}	Collector-Emitter Voltage	-20	V
V_{EBO}	Emitter-Base Voltage	-8	V
I_C	Collector Current	-5	A
P_C	Collector Power Dissipation	1.5	W
$R_{\theta JA}$	Thermal Resistance From Junction To Ambient	83	℃/W
T_j	Junction Temperature	150	℃
T_{stg}	Storage Temperature	-55~+150	℃

ELECTRICAL CHARACTERISTICS (T_a=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C= -1mA,I_E=0	-35			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C=-10mA,I_B=0	-20			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E= -1mA,I_C=0	-8			V
Collector cut-off current	I_{CBO}	V_{CB}=-35V,I_E=0			-100	μA
Emitter cut-off current	I_{EBO}	V_{EB}=-8V,I_C=0			-100	μA
DC current gain	$h_{FE(1)}$	V_{CE}=-2V, I_C=-0.5A	100		320	
	$h_{FE(2)}$	V_{CE}=-2V, I_C=-4A	70			
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=-4A,I_B=-0.1A			-1	V
Base-emitter voltage	V_{BE}	V_{CE}=-2V, I_C=-4A			-1.5	V
Collector output capacitance	C_{ob}	V_{CB}=-10V,I_E=0, f=1MHz		62		pF
Transition frequency	f_T	V_{CE}=-2V,I_C=-0.5A		170		MHz

CLASSIFICATION OF $h_{FE(1)}$

RANK	O	Y
RANGE	100-200	160-320

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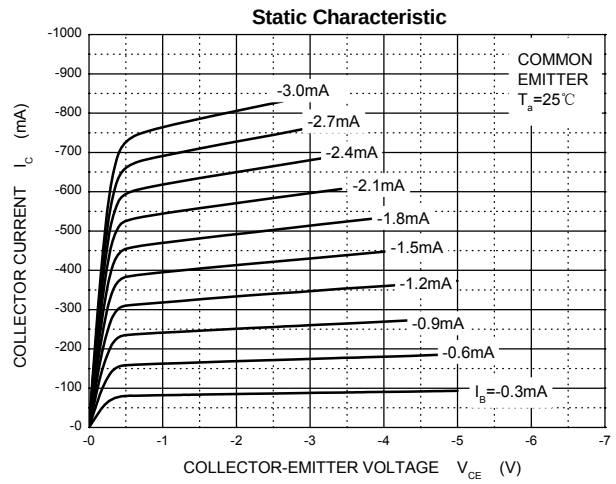
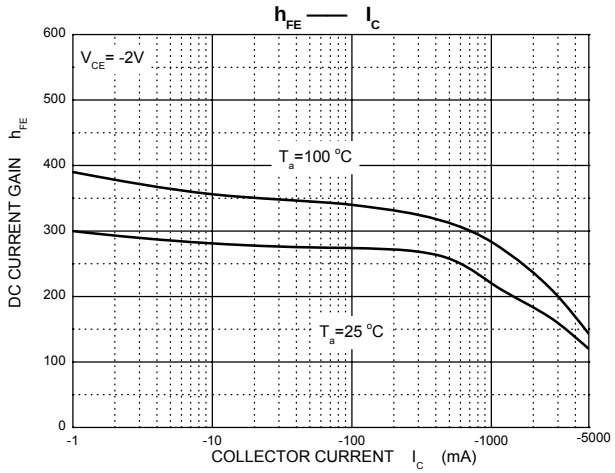
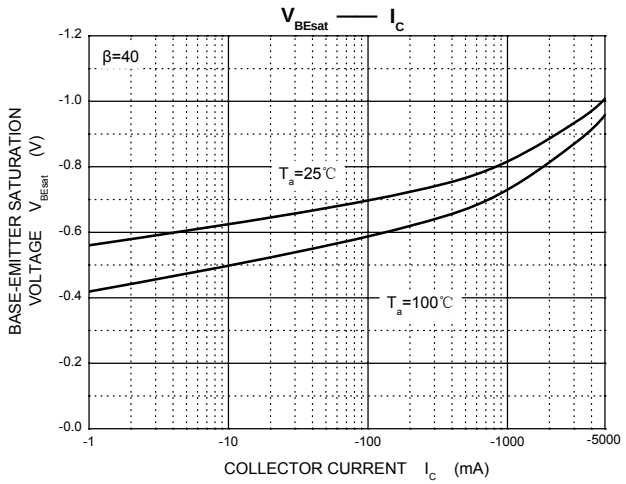
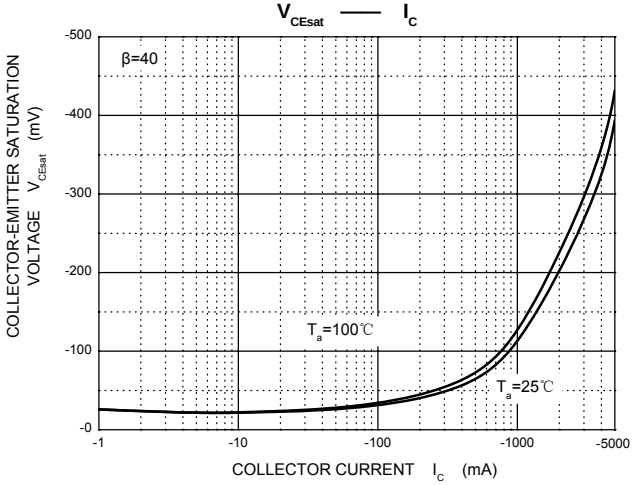
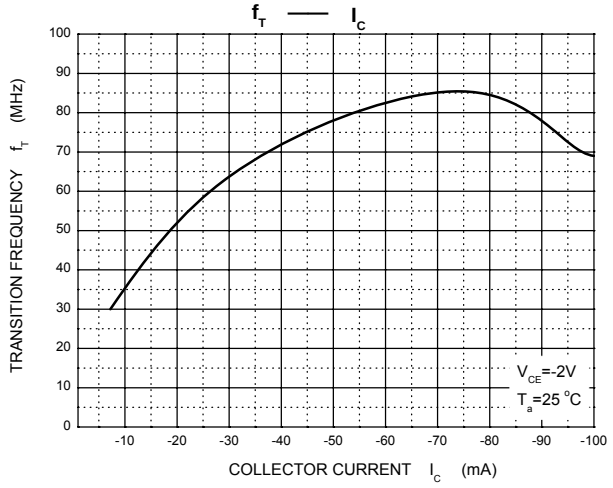
Typical Characteristics 2SA1357

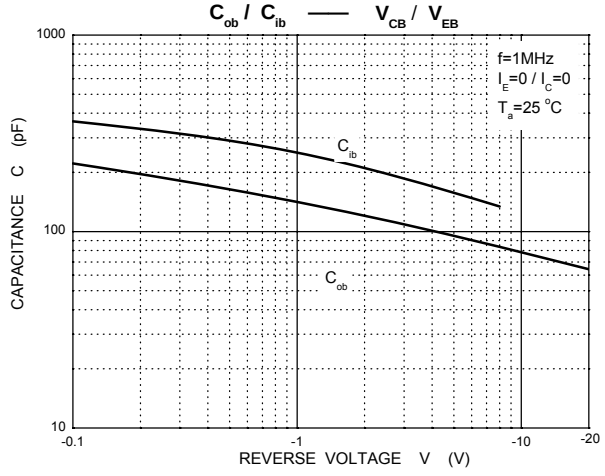


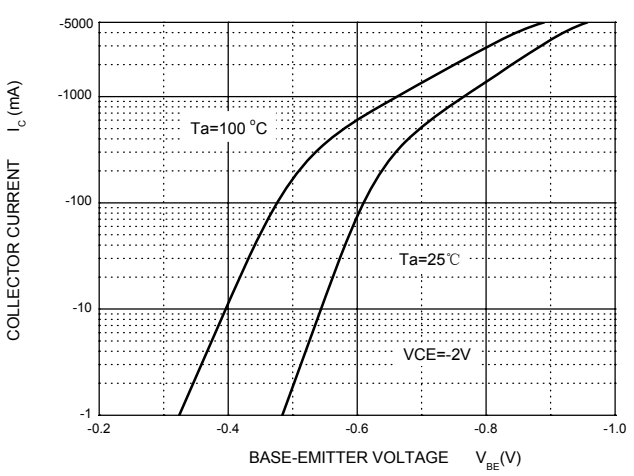


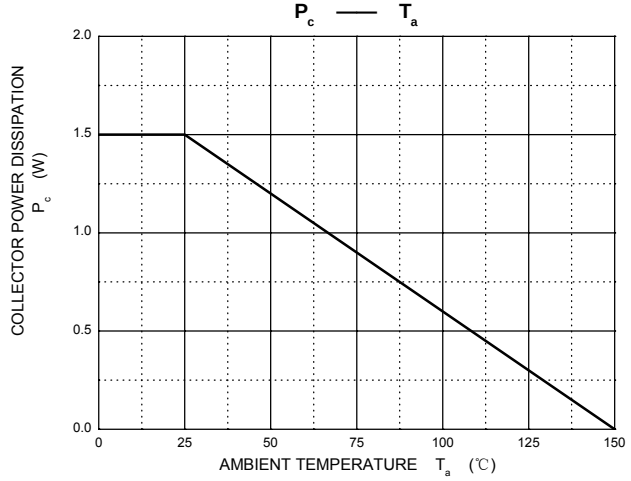












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